

### [h3] **Abstract of the Disclosure**

[p17] A method of forming retrograde n-wells and p-wells. A first mask is formed on the substrate and the n-well implants are carried out. Then the mask is thinned, and a deep p implant is carried out with the thinned n-well mask in place. This prevents  $V_t$  shifts in FETs formed in the n-well adjacent the nwell-pwell interface. The thinned mask is then removed, a p-well mask is put in place, and the remainder of the p-well implants are carried out.